

2P4M

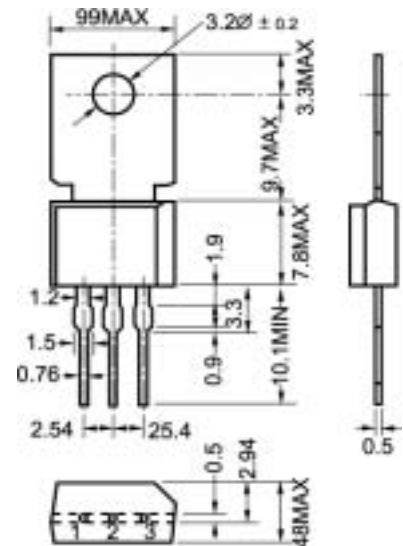
PLASTIC MOLDED THYRISTOR

◆ Features

- With TO-202 package
- 1cathode 2 anode 3 gate



K A G



◆ Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	400 (note: $R_{GK}=1k\Omega$)	V
V_{RRM}	Repetitive peak reverse voltage	400 (note: $R_{GK}=1k\Omega$)	V
$I_{T(AV)}$	On-state current	2($T_c=77^\circ$, $\theta=180^\circ$ Single phase(1/2wave))	A
I_{TSM}	Surge non-repetitive on-state current	20	A
P_{GM}	Peak gate power dissipation	0.5 (f $\geq$ 50Hz, Duty $\leq$ 10%)	W
$P_{G(AV)}$	Average gate power dissipation	0.1	W
I_{FGM}	Peak gate forward current	0.2 (f $\geq$ 50Hz, Duty $\leq$ 10%)	A
V_{RGM}	Peak gate reverse voltage	6	V
T_j	Junction temperature	-40 to + 125	

◆ Electrical characteristics (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_{RM}=V_{RRM}$, $T_j=125^\circ$, $R_{GK}=1k\Omega$		100	μA
I_{DRM}	Repetitive peak off-state current	$V_{DM}=V_{DRM}$, $T_j=125^\circ$, $R_{GK}=1k\Omega$		100	μA
V_{TM}	On-state voltage	$I_{TM}=4A$		1.8	V
I_{GT}	Gate-trigger current	$V_{DM}=6V$; $R_L=100\Omega$, $R_{GK}=1k\Omega$		100	μA
V_{GT}	Gate-trigger voltage	$V_{DM}=6V$; $R_L=100\Omega$, $R_{GK}=1k\Omega$		0.8	V
V_{GD}	Gate non-trigger voltage	$V_{DRM}=1/2V_{DRM}$, $T_j=125^\circ$, $R_{GK}=1k\Omega$	0.2		V
I_H	Holding current	$V_D=24V$; $R_{GK}=1k\Omega$, $I_{TM}=4A$		5	mA
$R_{th(j-c)}$	Thermal resistance	Junction to case		10	/W